



20V PNP LOW POWER TRANSISTOR IN SOT23

Features

- $BV_{CEO} > -20V$
- $BV_{ECO} > -7V$
- I_C = -4A Continuous Collector Current
- V_{CE(sat)} < -55mV @ -1A
- $R_{CE(sat)} = 34m\Omega$
- High Peak Current
- Complementary Part Number ZXTN25020CFH
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)

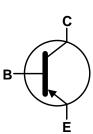
Applications

- MOSFET and IGBT Gate Driving
- **DC-DC Converters**

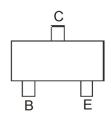
SOT23







Device Symbol



Top View Pin-Out

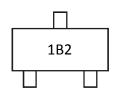
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP25020CFHTA	1B2	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1B2 = Product Type Marking Code

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Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-25	V
Collector-Emitter Voltage (Forward Blocking)	V _{CEO}	-20	V
Emitter-collector voltage (Reverse Blocking)	V _{ECO}	-7	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-4	Α
Base Current	I _B	-1	Α
Peak Pulse Current	I _{CM}	-10	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit		
	(Note 5)		0.73 5.84		
Power Dissipation	(Note 6)	D	1.05 8.4	W	
Linear derating factor	(Note 7)	P_D	1.25 9.6		
	(Note 8)		1.81 14.5		
	(Note 5) (Note 6)	_	171 119		
Thermal Resistance, Junction to Ambient	(Note 7) (Note 8)	$R_{ heta JA}$	100 69	°C/W	
Thermal Resistance, Junction to Lead	(Note 9)	R _{0JL}	74.95	°C/W	
Operating and Storage Temperature Range	_	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as note (5), except the device is surface mounted on 25mm x 25mm with 2 oz copper.
- 7. Same as note (5), except the device is surface mounted on 50mm x 50mm with 2 oz copper.
- 8. Same as note (7), except the device is measured at t<5secs.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).

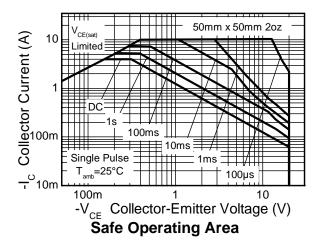
ESD Ratings (Note 10)

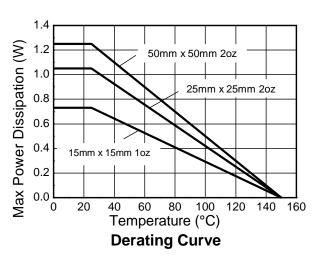
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

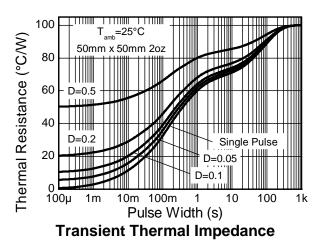
Note: 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

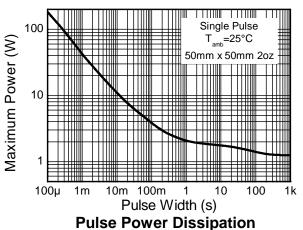


Thermal Characteristics and Derating Information











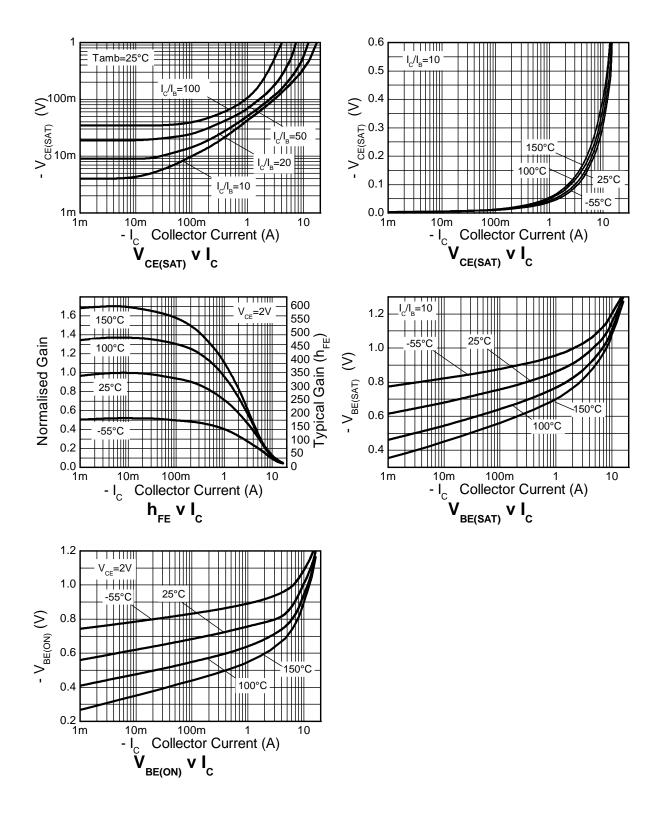
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-25	-50	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV_{CEO}	-20	-35	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.2	_	V	$I_E = -100 \mu A$
Emitter-Base Breakdown Voltage	BV _{ECO}	-7	-8.8	_	V	$I_E = -100 \mu A$
Collector-Base Cutoff Current	I _{CBO}	_	< -1	-50	nA	V _{CB} = -20V
Collector-Base Cuton Current		_	_	-20	μA	$V_{CB} = -20V, T_{amb} = +100$ °C
Emitter-Base Cutoff Current	I _{EBO}	_	< -1	-50	nA	$V_{EB} = -5.6V$
		200	350	500		$I_C = -10 \text{mA}, V_{CE} = -2 \text{V}$
0. 5 F 10 . T (B 5 (N . 44)		_	250	_		$I_C = -1A$, $V_{CE} = -2V$
Static Forward Current Transfer Ratio (Note 11)	h _{FE}	_	140	_	_	$I_C = -4A, V_{CE} = -2V$
		_	40	_		I _C = -10A, V _{CE} = -2V
	V _{CE(sat)}	_	-43	-55	1	$I_C = -1A$, $I_B = -100mA$
Collector Emitter Seturation Voltage (Note 11)		_	-70	-100		$I_C = -1A, I_B = -20mA$
Collector-Emitter Saturation Voltage (Note 11)		_	-120	-170		$I_C = -2A$, $I_B = -40mA$
		_	-150	-210		$I_C = -4A$, $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	_	-930	-1050	mV	$I_C = -4A$, $I_B = -200mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(on)}$	_	-810	-900	mV	I _C = -4A, V _{CE} = -2V
Output Capacitance	C _{obo}	_	32.4	40	pF	$V_{CB} = -10V$, $f = 1MHz$
Transition Frequency	f⊤	_	285	_	MHz	$V_{CE} = -10V, I_{C} = -50mA,$ f = 100MHz
Delay Time	t _(d)	_	38.4	_	nS	
Rise Time	t _(r)	_	49.2	_	nS	$V_{CC} = -15V, I_{C} = -750mA,$
Storage Time	t _(S)	_	168	_	nS	$I_{B1} = -I_{B2} = -15mA$
Fall Time	t _(f)	_	55	_	nS	

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

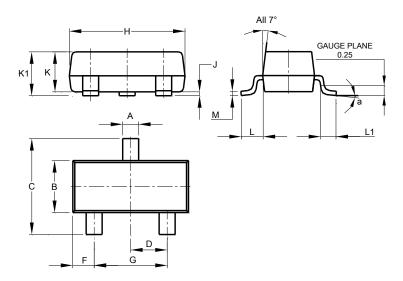




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT23

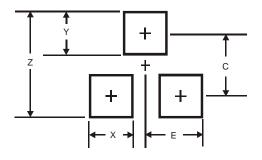


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT23



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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